BF393

High Voltage Transistor

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	300	Vdc
Collector - Base Voltage	V _{CBO}	300	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	I _C	500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above = 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

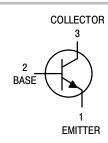
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



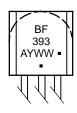
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



BF393 = Device Code A = Assembly Location

Y = Year
WW = Work Week
= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BF393	TO-92	5000 Units / Box
BF393G	TO-92 (Pb-Free)	5000 Units / Box
BF393ZL1	TO-92	2000 / Tape & Reel
BF393ZL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mAdc, I _B =0)	V _{(BR)CEO}	300	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \mu Adc, I_E = 0)$	V _{(BR)CBO}	300	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = 100 \mu Adc, I_C = 0)$	V _{(BR)EBO}	6.0	_	Vdc
Collector Cutoff Current (V _{CB} = 200 Vdc, I _E = 0)	I _{CBO}	-	0.1	μAdc
Emitter Cutoff Current (V _{EB} = 6.0 Vdc, I _C = 0)	I _{EBO}	-	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain $ \begin{aligned} \text{(I}_{\text{C}} &= 1.0 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc)} \\ \text{(I}_{\text{C}} &= 10 \text{ mAdc, V}_{\text{CE}} = 10 \text{ Vdc)} \end{aligned} $	h _{FE}	25 40	_ _	-
Collector – Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	V _{CE(sat)}	-	2.0	Vdc
Base – Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	V _{BE(sat)}	-	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	•	•	•	
Current Gain – Bandwidth Product ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 20 \text{ MHz}$)	f _T	50	-	MHz
Common Emitter Feedback Capacitance $(V_{CB} = 60 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{re}	_	2.0	pF

^{1.} Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%.

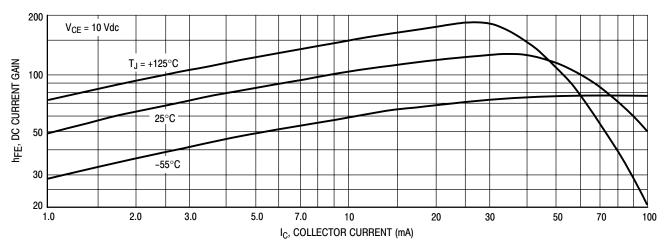


Figure 1. DC Current Gain

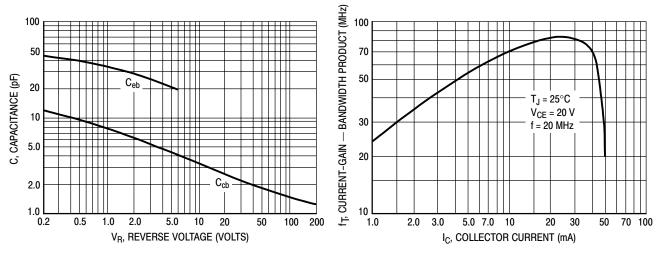


Figure 2. Capacitances

V, VOLTAGE (VOLTS)

500 1.4 $T_J = 25^{\circ}C$ 1.2 200 IC, COLLECTOR CURRENT (mA) 100 1.0 50 0.8 $V_{BE(sat)} @ I_C/I_B = 10$ 20 **CURRENT LIMIT** 0.6 10 V_{BE(on)} @ V_{CE} = 10 V THERMAL LIMIT 5.0 (PULSE CURVES @ $T_C = 25^{\circ}C$) 0.4 SECOND BREAKDOWN LIMIT 2.0 0.2 **CURVES APPLY** $V_{CE(sat)} @ I_C/I_B = 10$ MPSA43 BELOW RATED V_{CEO} 0.5 L 0.5 MPSA42 5.0 7.0 10 70 100 1.0 50 5.0 10 500 IC, COLLECTOR CURRENT (mA) V_{CE} , COLLECTOR-EMITTER VOLTAGE (VOLTS)

Figure 4. "On" Voltages

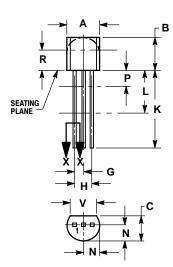
Figure 5. Maximum Forward Bias Safe Operating Area

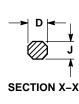
Figure 3. Current-Gain — Bandwidth Product

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PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 5M 1982
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	-
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1:

PIN 1. EMITTER
2. BASE
3. COLLECTOR

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